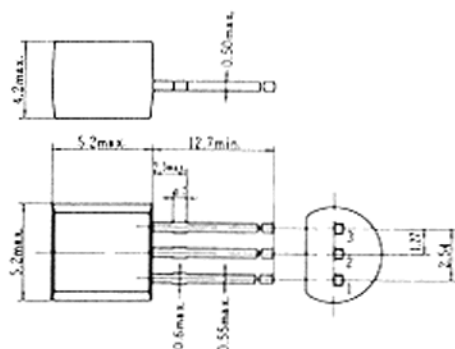


## 2SC1214

SILICON NPN EPITAXIAL  
LOW FREQUENCY AMPLIFIER



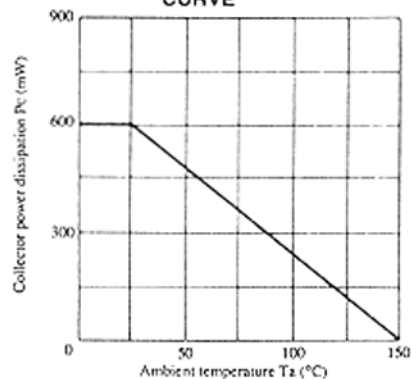
(JEDEC TO-92)

1. Emitter  
2. Collector  
3. Base  
(Dimensions in mm)

### ■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Item	Symbol	2SC1214	Unit
Collector to base voltage	V <sub>CB0</sub>	50	V
Collector to emitter voltage	V <sub>CE0</sub>	50	V
Emitter to base voltage	V <sub>EB0</sub>	4	V
Collector current	I <sub>C</sub>	500	mA
Collector power dissipation	P <sub>C</sub>	600	mW
Junction temperature	T <sub>J</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C

### MAXIMUM COLLECTOR DISSIPATION CURVE



### ■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

Item	Symbol	Test Condition	min.	typ.	max.	Unit
Collector to base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> = 10μA, I <sub>E</sub> = 0	50	—	—	V
Collector to emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> = 1mA, R <sub>BE</sub> = ∞	50	—	—	V
Emitter to base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> = 10μA, I <sub>C</sub> = 0	4	—	—	V
Collector cutoff current	I <sub>CB0</sub>	V <sub>CB</sub> = 20V, I <sub>E</sub> = 0	—	—	0.5	μA
DC current transfer ratio	h <sub>FE</sub> *	V <sub>CE</sub> = 3V, I <sub>C</sub> = 10mA	60	—	320	
	h <sub>FE</sub>	V <sub>CE</sub> = 3V, I <sub>C</sub> = 500mA (pulse test)	10	—	—	
Collector to emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> = 150mA, I <sub>B</sub> = 15mA	—	0.2	0.6	V
Base to emitter voltage	V <sub>BE</sub>	V <sub>CE</sub> = 3V, I <sub>C</sub> = 10mA	—	0.64	—	V

\* The 2SC1214 is grouped by h<sub>FE</sub> as follows.

B	C	D
60 to 120	100 to 200	160 to 320

■ See characteristic curves of 2SC1213.